
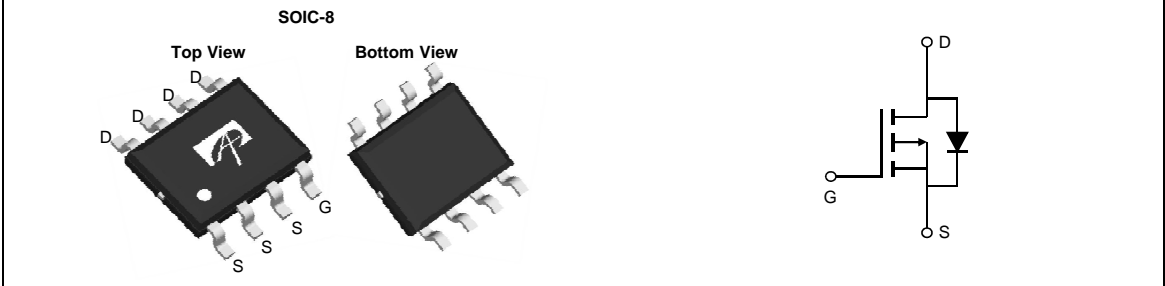


<p><b>General Description</b></p> <p>The AO4403 uses advanced trench technology to provide excellent <math>R_{DS(ON)}</math>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.</p>	<p><b>Product Summary</b></p> <table style="width: 100%; border: none;"> <tr> <td style="padding: 2px;"><math>V_{DS}</math></td> <td style="text-align: right; padding: 2px;">-30V</td> </tr> <tr> <td style="padding: 2px;"><math>I_D</math> (at <math>V_{GS}=-10V</math>)</td> <td style="text-align: right; padding: 2px;">-6A</td> </tr> <tr> <td style="padding: 2px;"><math>R_{DS(ON)}</math> (at <math>V_{GS}=-10V</math>)</td> <td style="text-align: right; padding: 2px;">&lt; 48m<math>\Omega</math></td> </tr> <tr> <td style="padding: 2px;"><math>R_{DS(ON)}</math> (at <math>V_{GS}=-4.5V</math>)</td> <td style="text-align: right; padding: 2px;">&lt; 57m<math>\Omega</math></td> </tr> <tr> <td style="padding: 2px;"><math>R_{DS(ON)}</math> (at <math>V_{GS}=-2.5V</math>)</td> <td style="text-align: right; padding: 2px;">&lt; 80m<math>\Omega</math></td> </tr> </table> <p style="margin-top: 10px;">100% UIS Tested 100% <math>R_g</math> Tested</p> <div style="text-align: right; margin-top: 10px;">  </div>	$V_{DS}$	-30V	$I_D$ (at $V_{GS}=-10V$ )	-6A	$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	< 48m $\Omega$	$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	< 57m $\Omega$	$R_{DS(ON)}$ (at $V_{GS}=-2.5V$ )	< 80m $\Omega$
$V_{DS}$	-30V										
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Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	-6	A
	$T_A=25^\circ\text{C}$		
	$T_A=70^\circ\text{C}$	-5	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	-30	
Avalanche Current <sup>C</sup>	$I_{AS}, I_{AR}$	18	A
Avalanche energy $L=0.1\text{mH}$ <sup>C</sup>	$E_{AS}, E_{AR}$	16	mJ
Power Dissipation <sup>B</sup>	$P_D$	3.1	W
	$T_A=70^\circ\text{C}$	2	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	31	40	$^\circ\text{C}/\text{W}$	
Maximum Junction-to-Ambient <sup>A,D</sup>		59	75	$^\circ\text{C}/\text{W}$	
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	$^\circ\text{C}/\text{W}$	

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.5	-0.9	-1.3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-30			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A T <sub>J</sub> =125°C		40 60	48 72	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A		45	57	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2A		60	80	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6A		19		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.7	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-3.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		645	780	pF
C <sub>oss</sub>	Output Capacitance			80		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			55		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	4	7.8	12	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(4.5V)</sub>	Total Gate Charge	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-6A		7		nC
Q <sub>gs</sub>	Gate Source Charge			1.5		nC
Q <sub>gd</sub>	Gate Drain Charge			2.5		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =2.5Ω, R <sub>GEN</sub> =6Ω		6.5		ns
t <sub>r</sub>	Turn-On Rise Time			3.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			41		ns
t <sub>f</sub>	Turn-Off Fall Time			9		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-6A, dI/dt=100A/μs		11		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-6A, dI/dt=100A/μs		3.5		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

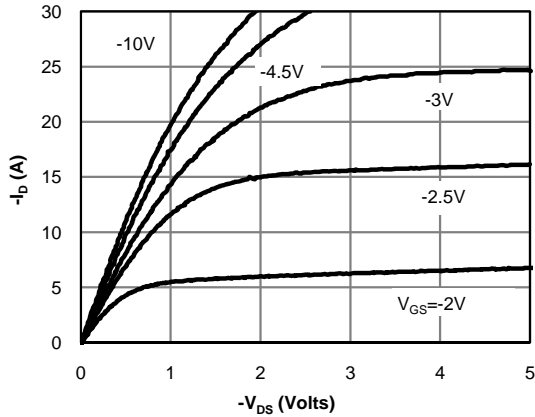
D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

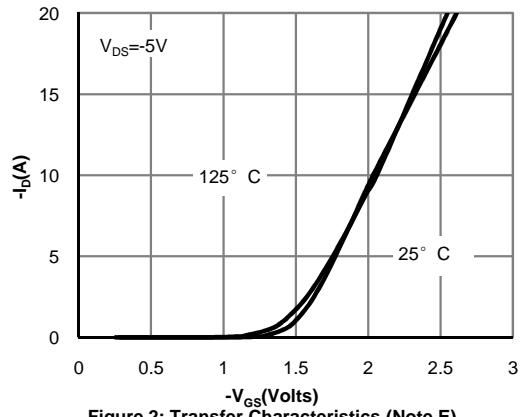
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

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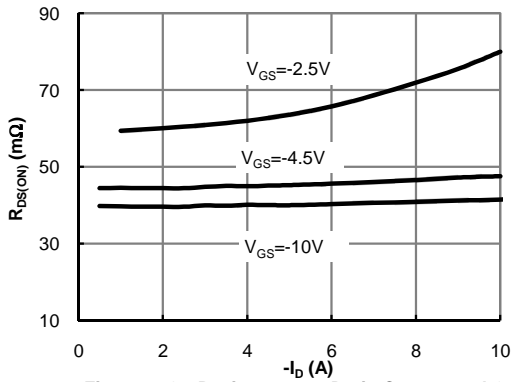
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



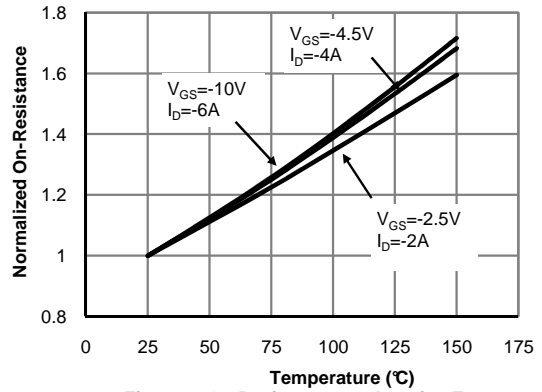
**Fig 1: On-Region Characteristics (Note E)**



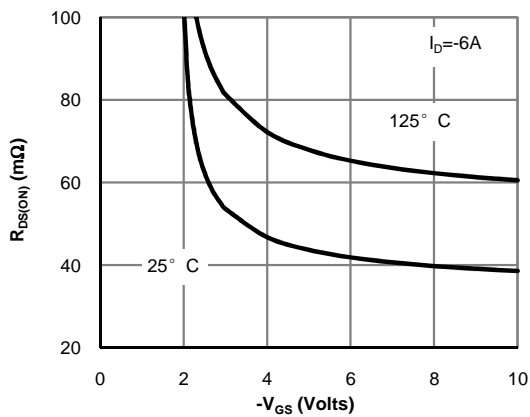
**Figure 2: Transfer Characteristics (Note E)**



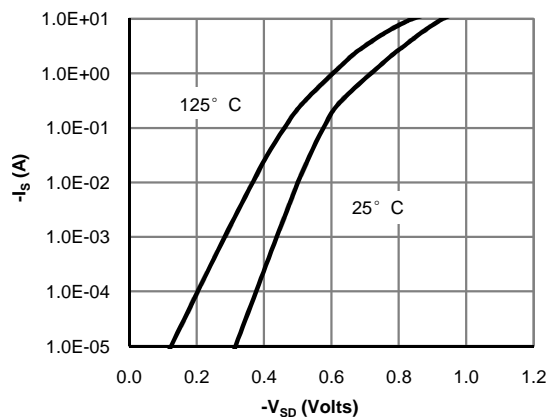
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

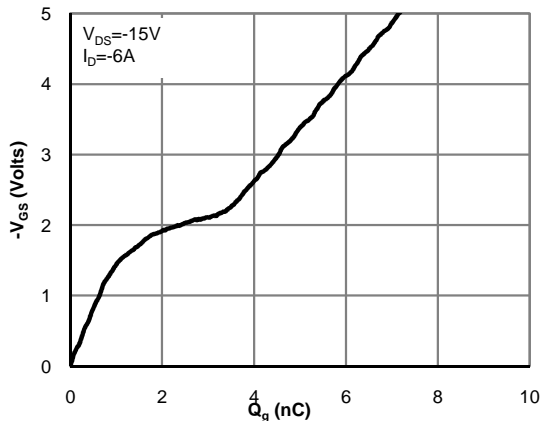


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

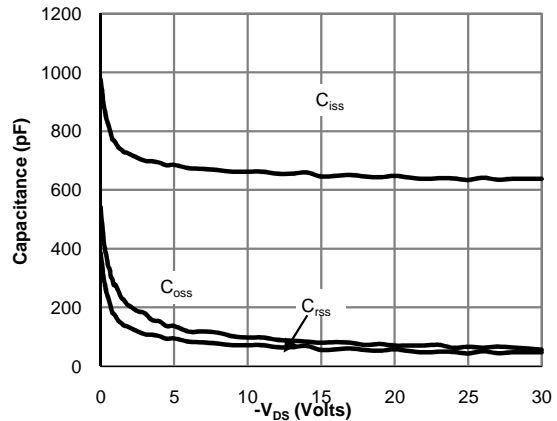


**Figure 6: Body-Diode Characteristics (Note E)**

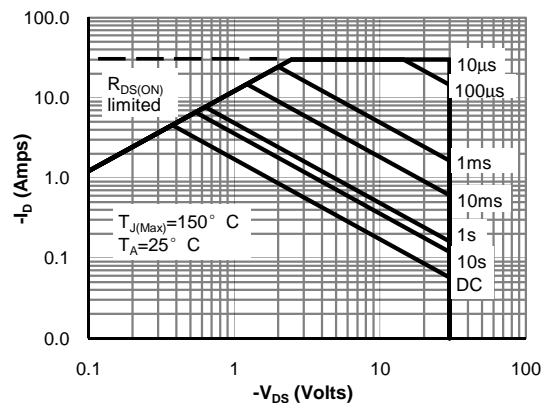
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



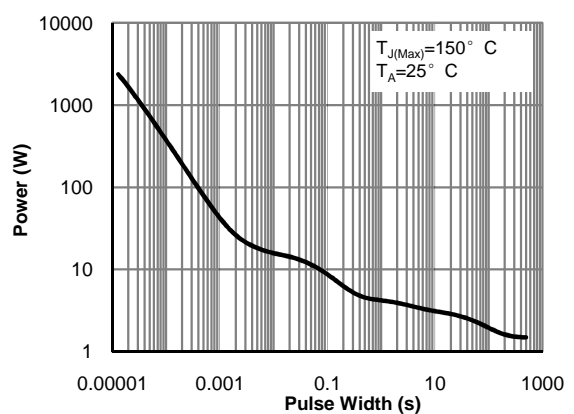
**Figure 7: Gate-Charge Characteristics**



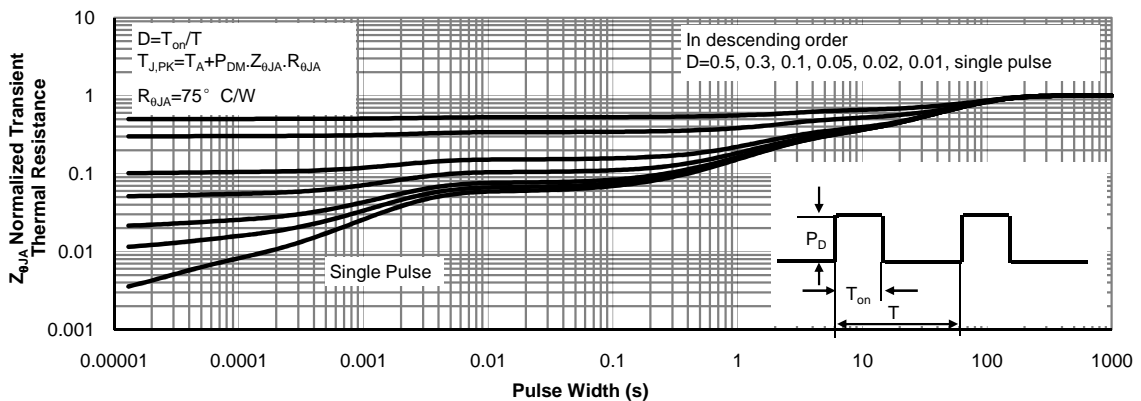
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**

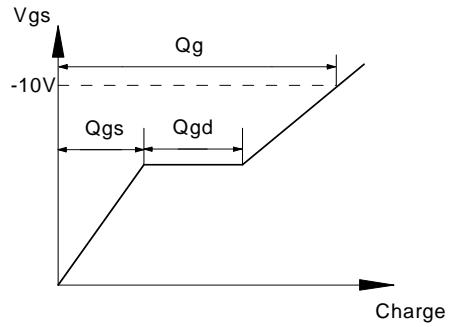
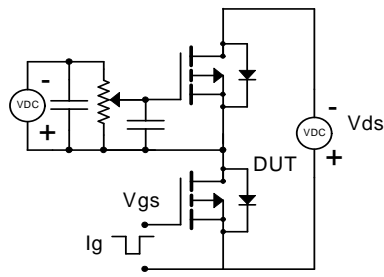


**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)**

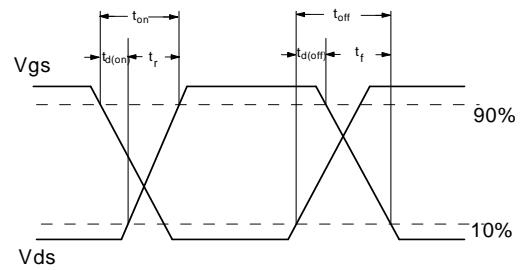
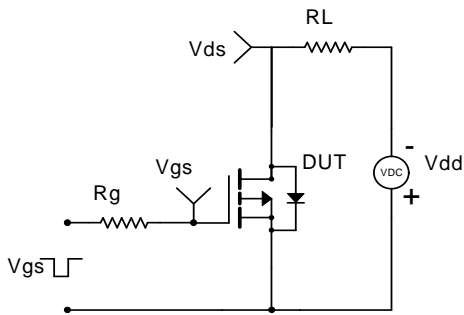


**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

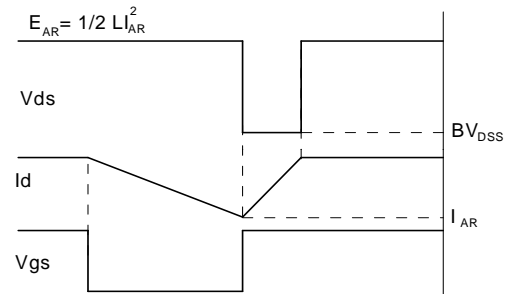
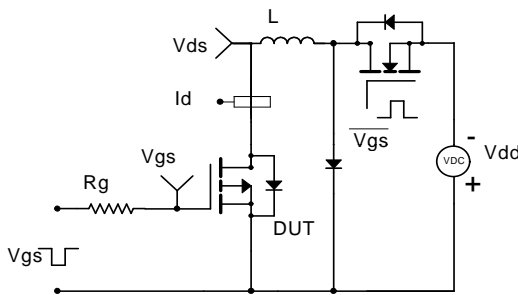
**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

